

Intrepid Atlas Direct Bonder

Direct Wafer Bonding:

A technique that "bonds" wafers together using plasma activation to create a hydrogen "bridge" between the two wafers. This pre-bonding step takes place at room temperature under a controlled environment. During a subsequent annealing step the low-energy hydrogen bridge bonds turn into covalent bonds.

Direct bonding is the key enabling technology for the SOI wafer fabrication process and for wafer-level 3D integration.

The Atlas Automated Direct Bonder performs all essential steps: cleaning, plasma activation, alignment, pre-bonding, and IR-inspection (optional). Thus, the Atlas Direct Bonder assures a high-yield, high-throughput (26 wph) processing of wafers up to 300 mm in size.

Features:

- Intrepid's low temp plasma activation
- Production system with a high-throughput, vacuum transport (estimated throughput of >\= to 26 wafer pair per hour)
- Automated cassette-to-cassette operation (load cassette platforms, SMIF or FOUP loaders)
- Contamination-free vacuum handling
- Super critical and/or chemical cleaning (optional)
- Pre-bonding with mechanical flat or notch alignment

Plasma Chamber

Proprietary Plasma Activation Module

- Proprietary plasma activation source/process
- Fully programable process, which includes control of all plasma variables ... Mass Flow Controller (4), Automated pressure control, RF power control, etc.
- Vacuum system: 9x10⁻² mbar (standard) and 9x10⁻³ mbar (option with turbo pump)
- Proprietary high energy RF source.

Pre-bond Station

Pre-bond Station

- Pre-bond is performed in Intrepid's unique vacuum pre-bond chamber
- Full environmental control: contact time, Force (up to 5 N) and gas type. Bond with full recipe control.
- Spacer free bonding (eliminates micro-voids and reduces particles)
- Advanced wafer flipping (performed in vacuum) eliminates chamber purge cycle contamination

Mechanical Alignment Station

In Vacuum Alignment Station

- Alignment type: flat-to-flat or notch-to-notch
- Alignment accuracy: X and Y: ± 5 µm, Theta: ± 0.1 °
- 100 300 mm wafer sizes

Clean Station (Optional)

Clean Station

- 3 standard processes: Super critical CO2, CO2 (Snow), or dilute RCA clean with hot N2 dry
- Single wafer processing with full recipe control
- Centering pin load system to assure alignment to eliminate unwanted vibration

IR Station (Optional)

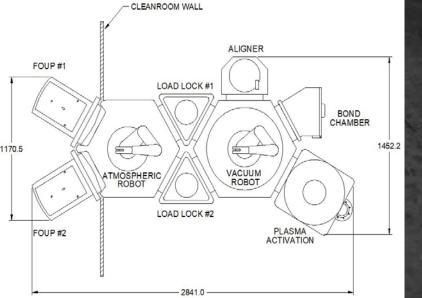
IR Station : For superior void detection

- 2 options available: ATM module (EFEM) or integrated with alignment module in vacuum
- LED illuminated with near IR LED array
- High sensitivity near IR camera for superior void detection

System Footprint: Intrepid vs EVG850LT



ATLAS BONDER

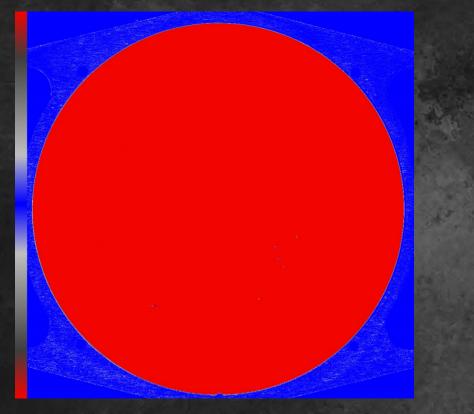


ATLAS LAYOUT

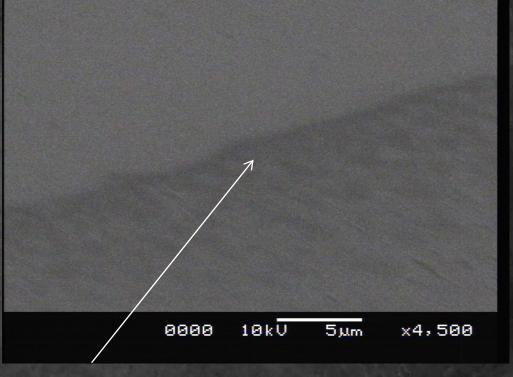


EVG850LT

Product Example



Scanning Acoustic Microscopy



Shear line showing removed material



Intrepid Equipment Corporation

1025 South 52nd Street, Tempe, Arizona 85281, United States

Phone: +1 (480) 968-8951

Email: info@intrepidequip.com